EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S64	2	("20020036004"|"5494526").PN.	US-PGPUB; USPAT; USOCR	AND	ON	2008/01/10 10:44
S65	12306	clean$3 and ((semiconductor or wafer or substrate) with ((upside with down) or suspended or upward))	US-PGPUB; USPAT; USOCR; EPO; JPO	AND	ON	2008/01/10 11:53
S66	16294	(wash$4 or clean$3 or rins$3) and ((semiconductor or wafer or substrate) with ((upside with down) or suspended or upward))	US-PGPUB; USPAT; USOCR; EPO; JPO	AND	ON	2008/01/10 11:54
S67	1126	(wash$4 or clean$3 or rins$3) near20 ((semiconductor or wafer or substrate) with ((upside with down) or suspended or upward))	US-PGPUB; USPAT; USOCR; EPO; JPO	AND	ON	2008/01/10 11:54
S68	119	(wash$4 or clean$3 or rins$3) near20 ((semiconductor or wafer or substrate) with ((upside with down) or suspended or upward)) near20 (nozzle)	US-PGPUB; USPAT; USOCR; EPO; JPO	AND	ON	2008/01/10 11:54
S69	132	(wash$4 or clean$3 or rins$3) near20 ((semiconductor or wafer or substrate) with ((upside with down) or suspended or upward)) near20 (nozzle or spray$3)	US-PGPUB; USPAT; USOCR; EPO; JPO	AND	ON	2008/01/10 12:00
S70	105	(wash$4 or clean$3 or rins$3) near20 (semiconductor or wafer or substrate) with (upside near2 down)	US-PGPUB; USPAT; USOCR; EPO; JPO	AND	ON	2008/01/10 12:02
S71	258	(wash$4 or clean$3 or rins$3) near20 (semiconductor or wafer or substrate) with ((fixed or mount$3) near4 (upper or ceiling or top))	US-PGPUB; USPAT; USOCR; EPO; JPO	AND	ON	2008/01/10 12:10
S72	50484	(upward$2 or (upside near2 down)) with (nozzle or spray)	US-PGPUB; USPAT; USOCR; EPO; JPO	AND	ON	2008/01/10 12:13
S73	50484	((upward$2 or (upside near2 down)) with (nozzle or spray))	US-PGPUB; USPAT; USOCR; EPO; JPO	AND	ON	2008/01/10 12:13
S74	258	((upward$2 or (upside near2 down)) with (nozzle or spray)) with (wash$4 or clean$3 or rins$3) with (semiconductor or wafer or substrate)	US-PGPUB; USPAT; USOCR; EPO; JPO	AND	ON	2008/01/10 12:14

EAST Search History

S75	381	(((upward$2 or (upside near2 down)) with (nozzle or spray))) same ((wash$4 or clean$3 or rins$3) with (semiconductor or wafer or substrate))	US-PGPUB; USPAT; USOCR; EPO; JPO	AND	ON	2008/01/10 12:14
S76	381	S74 or S75	US-PGPUB; USPAT; USOCR; EPO; JPO	AND	ON	2008/01/10 13:54
S77	2612	134/902.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	AND	ON	2008/01/10 14:43
S78	32	134/902.ccls. and (upside near2 down)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	AND	ON	2008/01/10 14:01
S79	6	("5357991").URPN.	USPAT	OR	OFF	2008/01/10 14:03
S80	6	("5357991").URPN.	USPAT	OR	OFF	2008/01/10 14:03
S81	107	(wash$4 or clean$3 or rins$3) with (semiconductor or wafer or substrate) with (upside near2 down)	US-PGPUB; USPAT; USOCR; EPO; JPO	AND	ON	2008/01/10 14:04
S82	14	(wash$4 or clean$3 or rins$3) with (semiconductor or wafer or substrate) with (upside near2 down)	EPO; JPO; DERWENT	AND	ON	2008/01/10 14:53
S83	12	(wash$4 or clean$3 or rins$3) near15 (semiconductor or wafer or substrate) near15 (upside near2 down)	EPO; JPO; DERWENT	AND	ON	2008/01/10 14:04
S84	209	134/902.ccls. and patterned	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	AND	ON	2008/01/10 14:43
S85	253	(wash$4 or clean$3 or rins$3) with (patterned with (semiconductor or wafer or substrate))	EPO; JPO; DERWENT	AND	ON	2008/01/10 14:44
S86	38	(wash$4 or clean$3 or rins$3) with (semiconductor or wafer or substrate) with ((nozzle or jet) near4 (upward$2) or (upside near2 down))	EPO; JPO; DERWENT	AND	ON	2008/01/10 14:53